

Please amend the following claims to the state indicated below.

- A2 Sub 33
1. (Once amended) A process of PECVD deposition of metal films comprising the steps of:
providing an ion promoting atmosphere; and
contacting a substrate with a plasma of approximately 50 to 90 % of a metal-
containing gas in said ion promoting atmosphere at a pressure and temperature
range sufficient for film deposition for said metal.

- A3
29. (Once amended) A process for PECVD deposition of metal-containing films on a surface,
the process comprising:

maintaining a pressure and a temperature which allow for PECVD metal-containing
film deposition; and
contacting said surface with a plasma of approximately 50 to 90% metal-
containing compound in a chemically inert atmosphere.

A marked-up version of these amended claims appears in an appendix to this Preliminary
Amendment.

REMARKS

Claims 1-66 are part of the original specification.

Claims 5-28 and 30-66 are cancelled without prejudice.

Claims 1 and 29 are amended.

Claims 1-4, and 29 are pending.

Applicants note that the specification of this continuation has been altered from that of the
parent by providing paragraph numbering and by fixing a typographical error in the title as it
appears on page 1, after the cover page.

In the interest of efficient prosecution, Applicants also note that claims 1-4 and 29 were
prosecuted in the parent application and rejected in an Office Action dated February 9, 2001